

Strain and Defect – Engineered Modulation of Structural, Optical, and Magnetic Properties in Ho³⁺ Doped β -Ga₂O₃ Nanoparticles

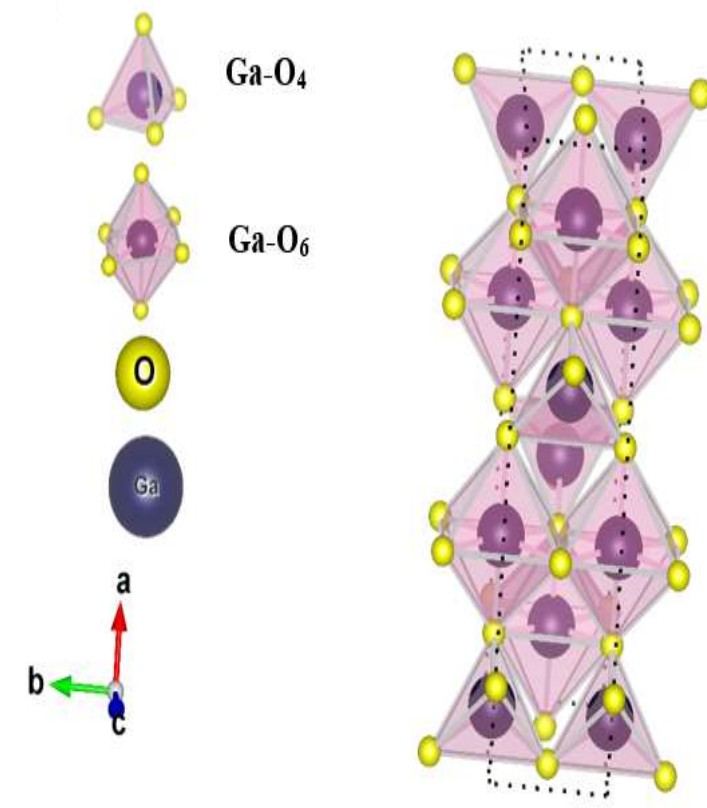
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INTRODUCTION & AIM

- ✓ β -Ga₂O₃ is an ultra-wide bandgap semiconductor (~4.8 eV) known for its exceptional thermal and chemical stability.
- ✓ To date, the effects of holmium (Ho) doping in beta-gallium oxide (β -Ga₂O₃) have not yet been investigated.
- ✓ Doping with Ho³⁺ ions, which possess a larger ionic radius and rich 4f electronic states, introduces controlled lattice strain and defect states, enabling the modulation of structural, optical, and magnetic properties.
- ✓ This defect-engineering strategy tailors material functionalities, making Ho³⁺-doped β -Ga₂O₃ a promising multifunctional material.



METHOD

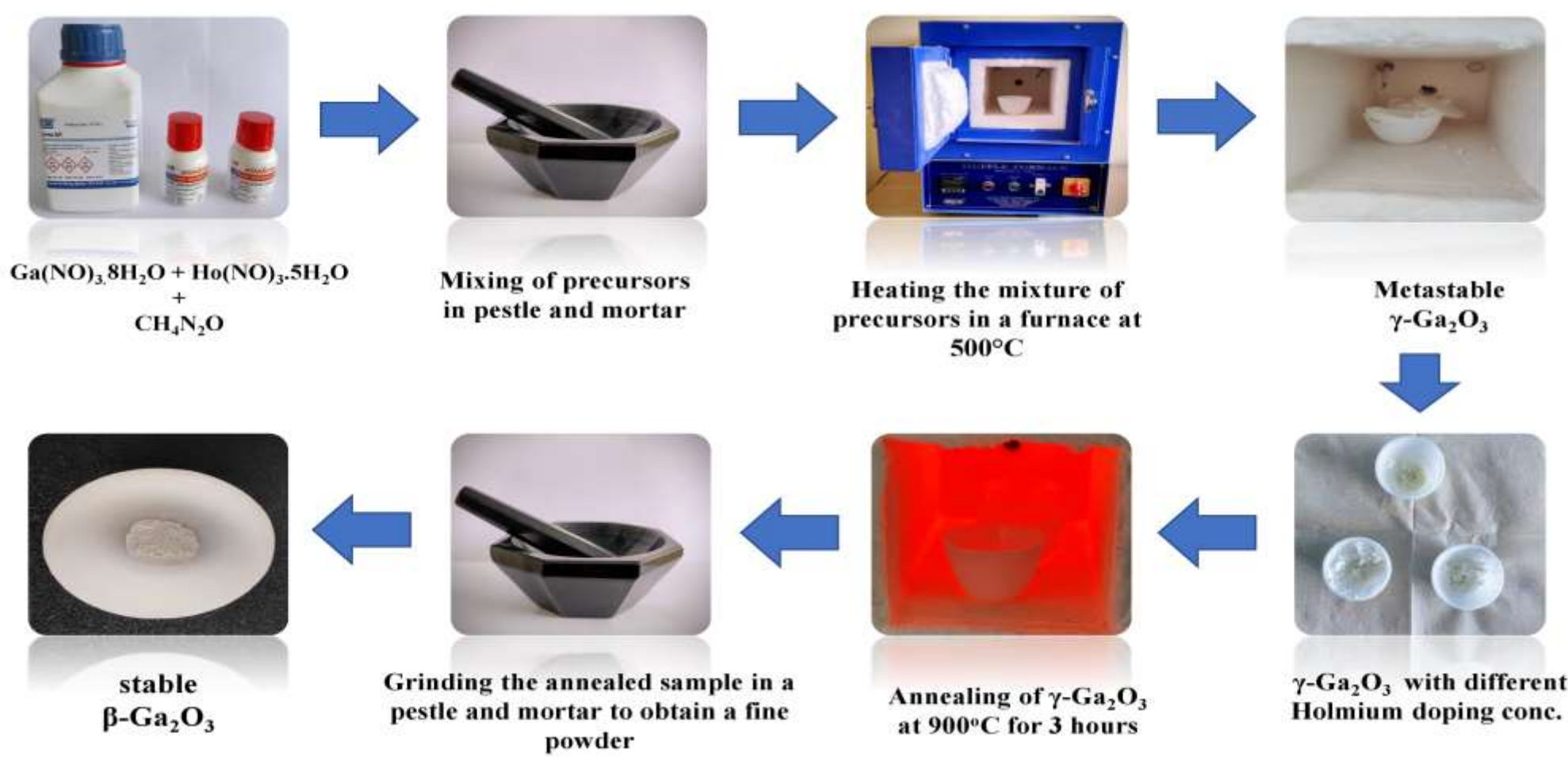


Table 1: Structural parameters of Holmium doped β -Ga₂O₃ samples

Samples	β - GOH-1	β - GOH - 2	β - GOH - 3
2 θ (deg)	31.71	31.75	31.75
FWHM β (deg)	0.3824	0.3038	0.2955
W-H Size DW-H	9.65	11.49	11.73
DW-H Dislocation Density ($\delta \times 10^{-3} \text{ (nm}^{-2}\text{)}$)	10.738	7.574	7.267
Strain ($\epsilon \times 10^{-3}$)	-2.94	2.52	-2.41

CONCLUSION

- ✓ The crystallite size exhibits a non-uniform trend, initially decreasing at 1 % Ho doping and then partially recovering at higher concentrations.
- ✓ Williamson-Hall analysis reveals the presence of compressive lattice strain, which progressively relaxes with increasing Ho concentration.
- ✓ UV-Vis absorption analysis shows a systematic blue shift in the absorption edge, indicating an increase in the optical bandgap energy upon Ho incorporation.
- ✓ Photoluminescence spectra display pronounced quenching of emission intensity, suggesting the activation of non-radiative recombination channels with increasing Ho content.
- ✓ Magnetic measurements show that pure β -Ga₂O₃ exhibits diamagnetic behavior, whereas Ho-doped samples display progressively stronger paramagnetic responses with increasing Ho concentration, without showing any magnetic hysteresis.

ACKNOWLEDGEMENT

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FUTURE WORK / REFERENCES

For future study, we can investigate the upconversion in our holmium-doped sample by exciting it with a near-infrared laser and analyzing the subsequent higher-energy visible light emission.

- Sharma, Abhishek, and Vir Singh Rangra. "Effect of gadolinium doping on the structural, morphological, vibrational, and optical properties of β -Ga₂O₃: a solid-state combustion approach." *Ceramics International* 51.13 (2025): 17583-17592.

RESULTS & DISCUSSION

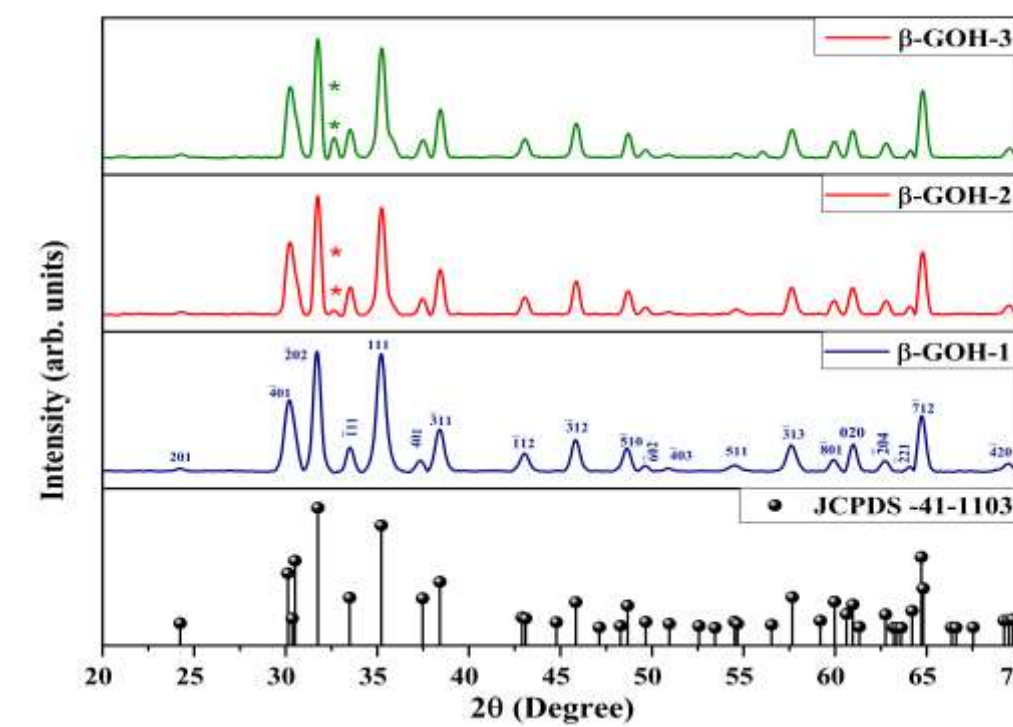


Fig.1 XRD spectra of Holmium doped samples at 1, 2 and 3 wt. %

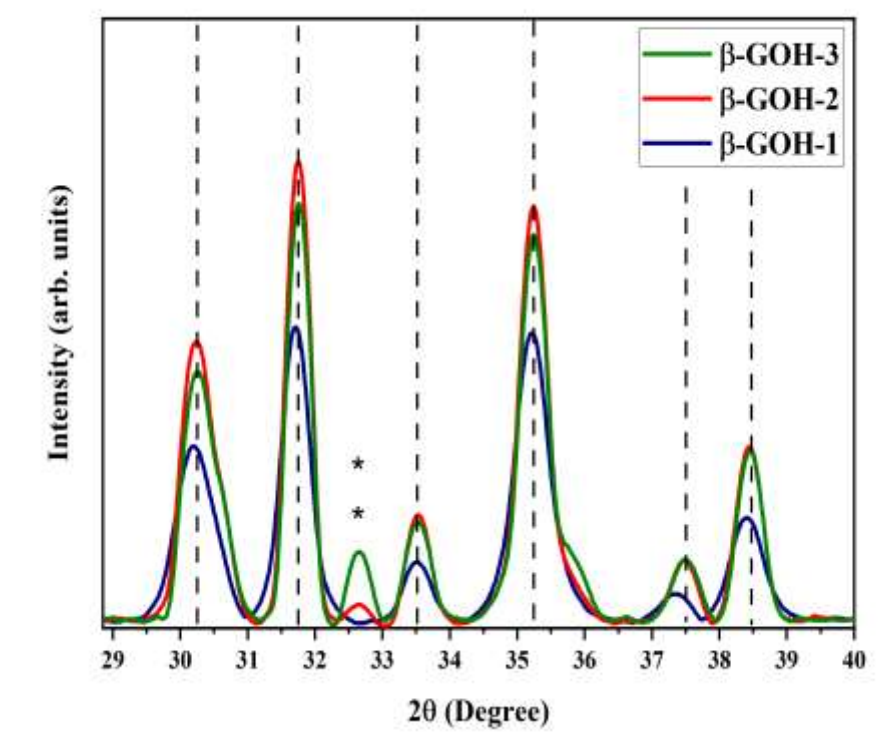


Fig2. Shifts in XRD peaks

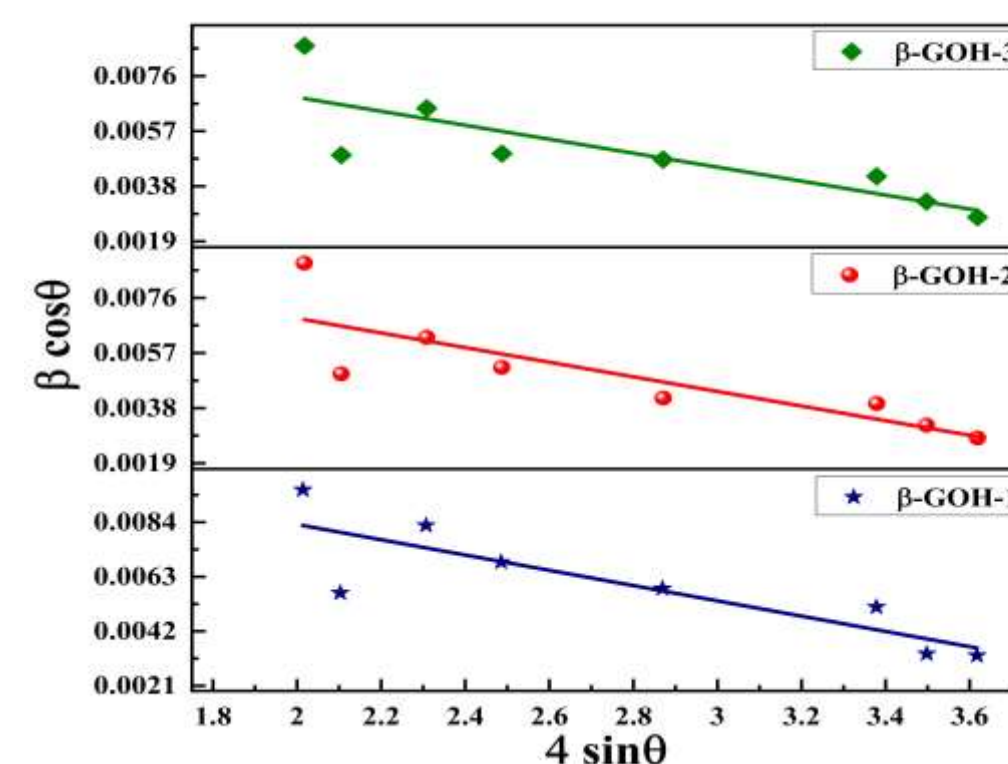


Fig.3 Williamson-Hall (W-H) plot

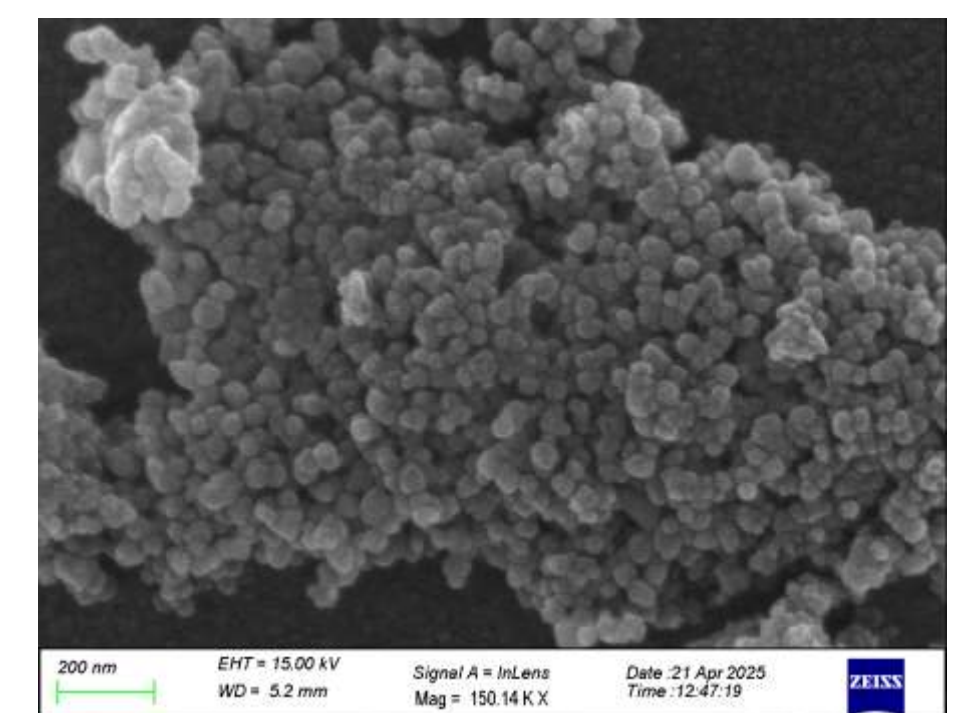


Fig4. FESEM micrograph of Holmium doped samples at 1% wt.% concentration

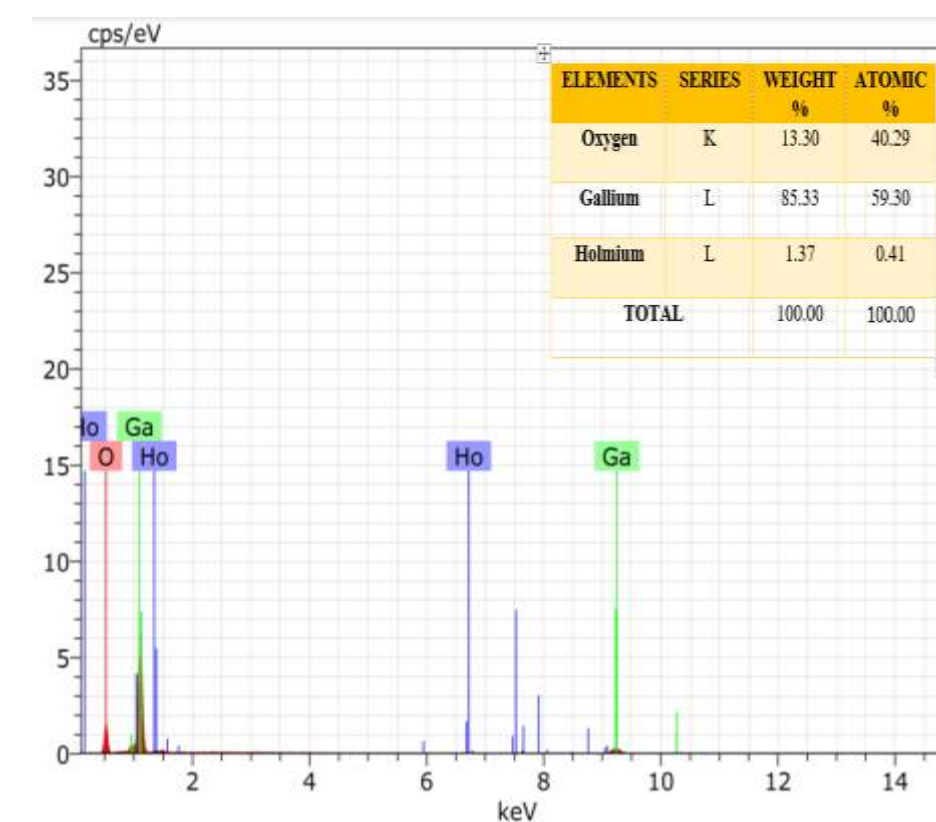


Fig.5 Holmium doped samples at 1% wt.% concentration

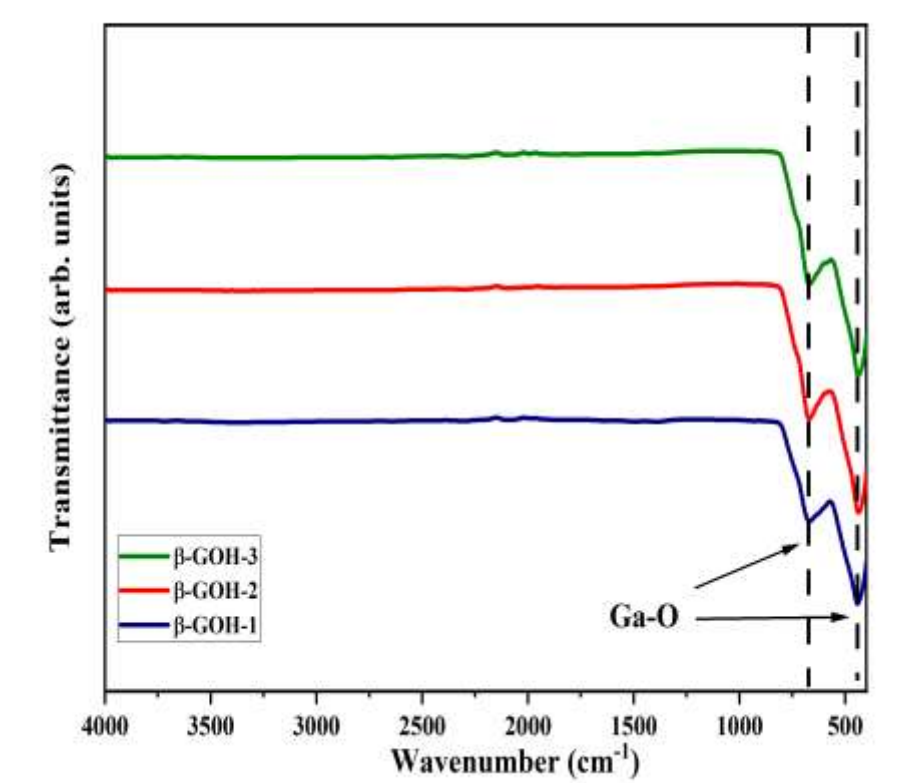


Fig. 6 FTIR Spectra

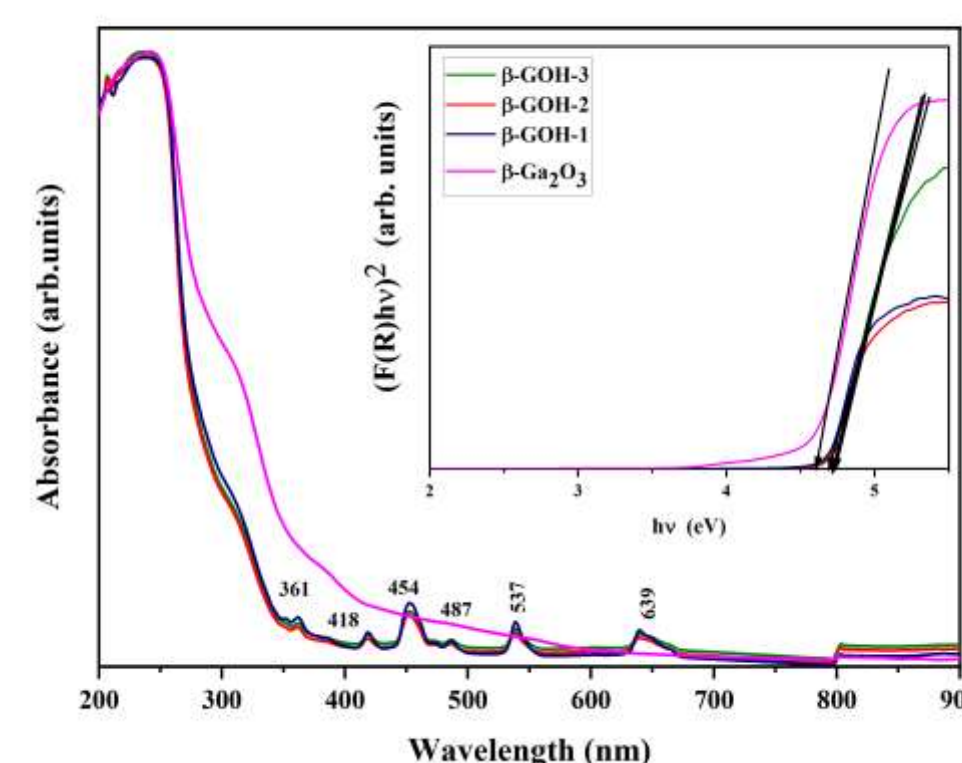


Fig8. Absorbance Spectra of pure and Holmium doped samples

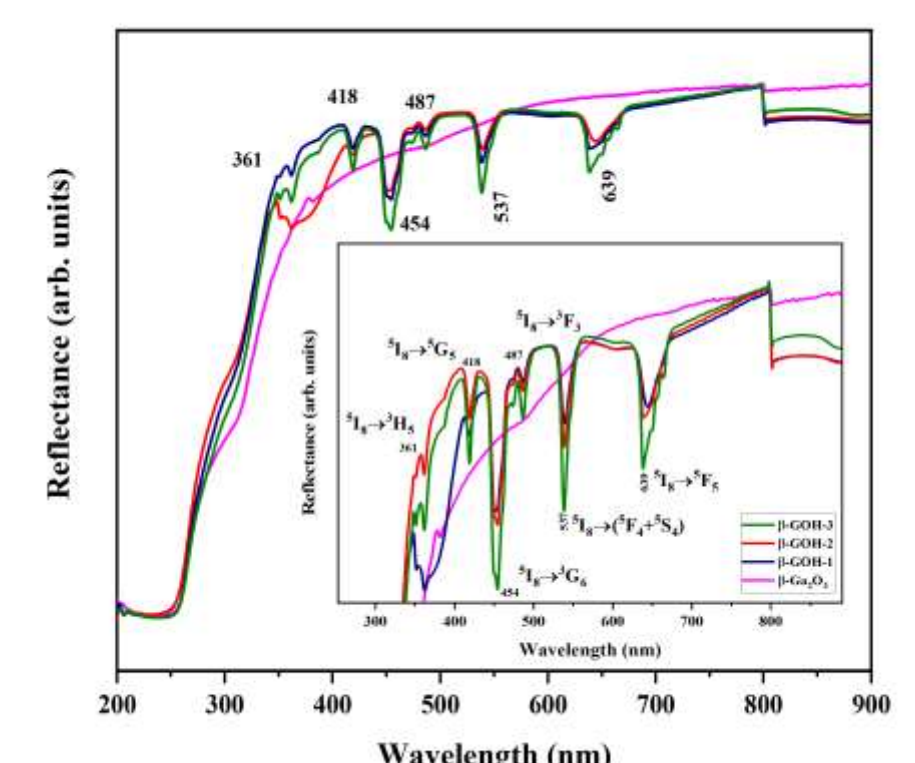


Fig9. Reflectance Spectra

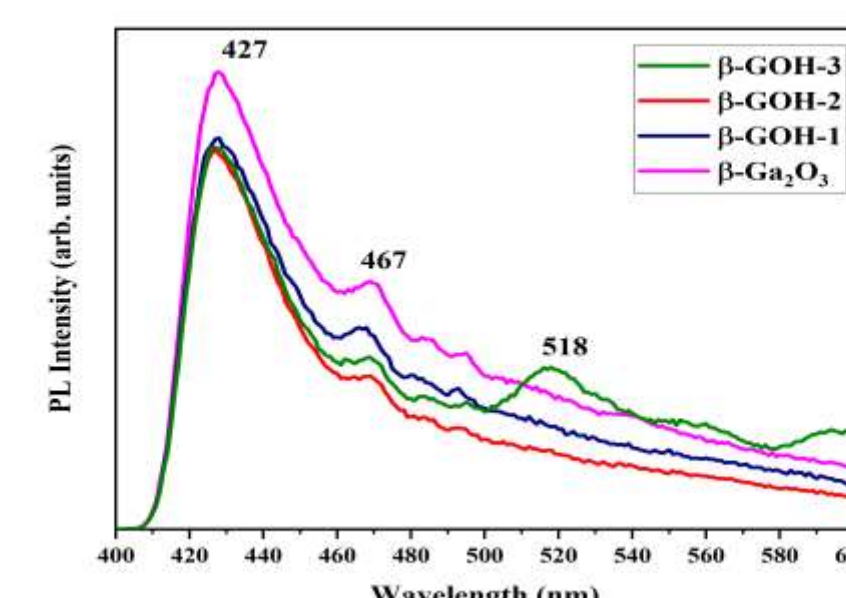


Fig9. PL Spectra of pure and Holmium doped samples

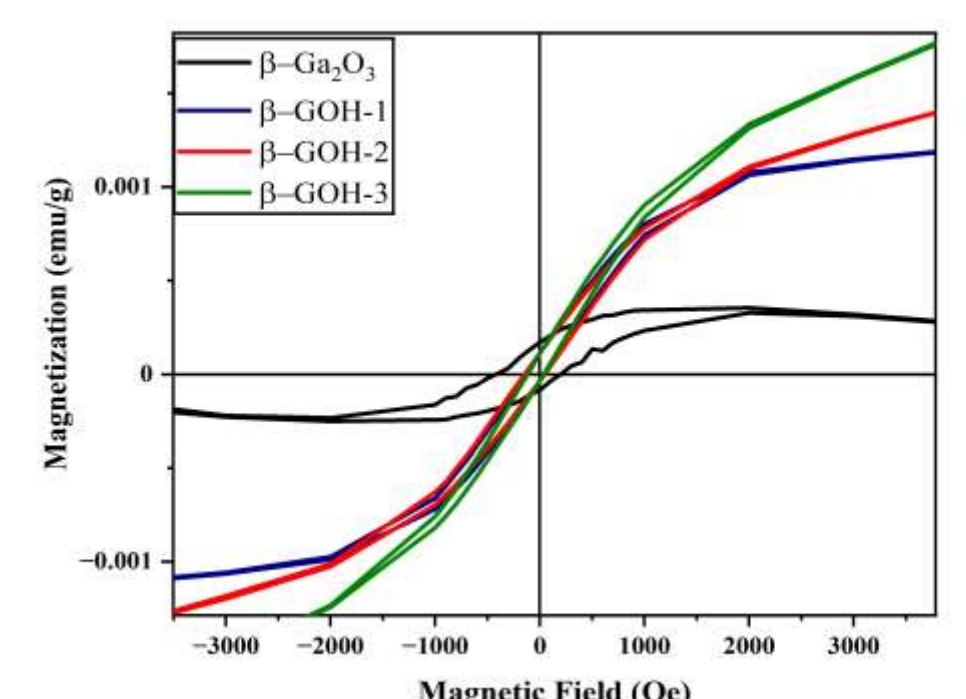


Fig10. Magnetic Hysteresis(M-H) loop of pure and Holmium doped samples